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LIST OF PATENT INFORMATION I	TS AND PUBLICATIONS I	FOR APPLICANT'S NT	APPLICANT: K. Hayashi et al.			S. 57	
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	OTHER	RART (Including A	Author, Title, Date, Pertir	nent Pages, etc	.)		
WY	J. Moodera et al., "	Ferromagnetic-insulator-	ferromagnetic tunneling: Spin-dep	endent tunneling an	d large magnetore	esistance in	trilayer
	junctions (invited)", J. Appl. Phys. 79 (8), April 15, 1996 D. Thompson et al., "Thin film magnetoresistors in memory, storage, and related applications", IEEE Transactions on Magnetics, Vol						
WK	D. Thompson et al., Mag-11, No. 4, July	-	stors in memory, storage, and rela	ited applications", I	EEE Transactions	on Magne	tics, Vo
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